



DEPOSITION SYSTEMS FOR COMPOUND SEMICONDUCTORS

AIX 2800G4-TM

for GaAs/InP based Optoelectronics and p-HEMT/HBT Devices

AIXTRON

Our technology. Your future.

Increase your capacity and take advantage of highest yield

AIX 2800G4-TM MOCVD System

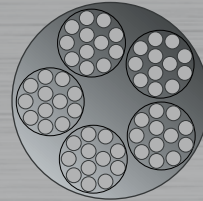
Your Benefit

- ▶ Highest device yield & throughput
- ▶ High precursor & hydride efficiencies
- ▶ Lowest cost/wafer
- ▶ Flexible configuration for 2 to 8 inch

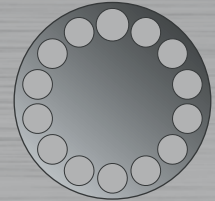
Design Highlights

- ▶ Automated satellite loading
- ▶ Triple gas injector
- ▶ Latest reactor design featuring
 - Advanced process tuning
 - Increased process robustness
 - Minimized overall maintenance

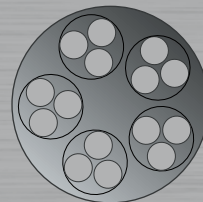
Available Susceptor Configurations



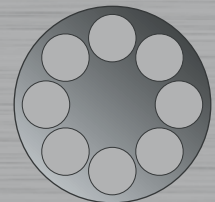
60 x 2 inch



14 x 3 inch



15 x 4 inch

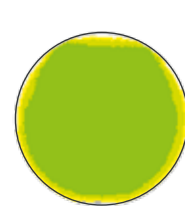


8 x 6 inch

Process and Transfer Module

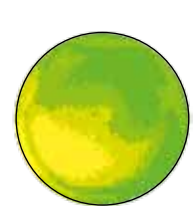


4 inch ALGaInP MQW results



**PL wavelength
uniformity (avg. 617 nm)**

0.6 nm standard
deviation without EE



**FWHM uniformity
(avg. 27 meV)**

1.7 % standard
deviation without EE

